

## **Gate Driver Providing Galvanic isolation Series**

## Isolation voltage 2500Vrms 1ch Gate Driver Providing Galvanic Isolation

## BM60054FV-C

#### **General Description**

The BM60054FV-C is a gate driver with isolation voltage 2500Vrms, I/O delay time of 110ns, and a minimum input pulse width of 90ns. Fault signal output function, ready signal output function, under voltage lockout (UVLO) function, short current protection (SCP) function, and switching controller function are all built-in.

#### Features

- Provides Galvanic Isolation
- Fault Signal Output Function
- Ready Signal Output Function
- Under Voltage Lockout Function
- Short Circuit Protection Function
- Soft Turn-Off Function for Short Circuit Protection (Adjustable Turn-OFF time)
- Thermal Protection Function
- Active Miller Clamping
- Switching Controller Function
- Output State Feedback Function
- UL1577 Recognized:File No. E356010
- AEC-Q100 Qualified<sup>(Note 1)</sup>
- (Note 1:Grade1)

#### Applications

- Driving IGBT Gate
- Driving MOSFET Gate

#### **Typical Application Circuit**

#### Key Specifications

- Isolation Voltage:
- Maximum Gate Drive Voltage:
- I/O Delay Time:
- Minimum Input Pulse Width:

Package SSOP-B28W W(Typ) x D(Typ) x H(Max) 9.2 mm x 10.4 mm x 2.4 mm

2500Vrms

20V(Max)

110ns(Max)

90ns(Max)

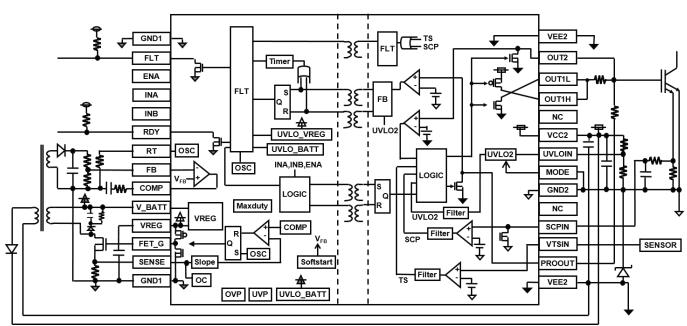


Figure 1. Typical Application Circuit

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## Datasheet

## **Recommended Range of External Constants**

Pin Name			nmended	Value	Unit
Fin Name	Symbol	Min	Тур	Max	Unit
VREG		1.0	3.3	10.0	μF
VCC2	CVCC2	0.33	-	-	μF
RT	R <sub>RT</sub>	24	68	150	kΩ

## **Pin Configuration**

	_	(TOP VIEW)		
VEE2	1	$\bigcirc$	28	GND1
PROOUT [	2		27	SENSE
VTSIN	3		26	FET_G
SCPIN	4		25	VREG
NC	5		24	V_BATT
GND2	6		23	COMP
MODE	7		22	FB
UVLOIN	8		21	RT
VCC2	9		20	RDY
NC [	10		19	] INB
OUT1H	11		18	INA
OUT1L	12		17	] ENA
OUT2	13		16	] FLT
VEE2	14		15	GND1

## **Pin Descriptions**

	Pin Name	Pin Function
1	VEE2	Output-side negative power supply pin
2	PROOUT	Soft turn-off pin / Gate voltage input pin
3	VTSIN	Thermal detection pin
4	SCPIN	Short circuit current detection pin
5	NC	No connection
6	GND2	Output-side ground pin
7	MODE	Mode selection pin of output-side UVLO
8	UVLOIN	Output-side UVLO setting pin
9	VCC2	Output-side positive power supply pin
10	NC	No connection
11	OUT1H	Source side output pin
12	OUT1L	Sink side output pin
13	OUT2	Output pin for Miller Clamp
14	VEE2	Output-side negative power supply pin
15	GND1	Input-side ground pin
16	FLT	Fault output pin
17	ENA	Input enabling signal pin
18	INA	Control input pin A
19	INB	Control input pin B
20	RDY	Ready output pin
21	RT	Switching frequency setting pin for switching controller
22	FB	Error amplifier inverting input pin for switching controller
23	COMP	Error amplifier output pin for switching controller
24	V_BATT	Main power supply pin
25	VREG	Input-side internal power supply pin
26	FET_G	MOS FET control pin for switching controller
27	SENSE	Current detection pin for switching controller
28	GND1	Input-side ground pin

## **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Main Power Supply Voltage	VBATT	-0.3 to +40.0 <sup>(Note 2)</sup>	V
Output-Side Positive Supply Voltage	V <sub>CC2</sub>	-0.3 to +24.0 <sup>(Note 3)</sup>	V
Output-Side Negative Supply Voltage	V <sub>EE2</sub>	-15.0 to +0.3 <sup>(Note 3)</sup>	V
Maximum Difference Between Output-Side Positive and Negative Voltages	V <sub>MAX2</sub>	30.0	V
INA, INB, ENA Pin Input Voltage	VIN	-0.3 to +7.0 <sup>(Note 2)</sup>	V
MODE Pin Input Voltage	VMODE	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	V
SCPIN Pin Input Voltage	VSCPIN	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	V
VTSIN Pin Input Voltage	Vvts	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	V
UVLOIN Pin Input Voltage	V <sub>UVLOIN</sub>	-0.3 to +VCC2+0.3 or +24.0 <sup>(Note 3)</sup>	V
OUT1H, OUT1L Pin Output Current (Peak 10µs)	IOUT1PEAK	5.0 <sup>(Note 4)</sup>	А
OUT2 Pin Output Current (Peak 10µs)	IOUT2PEAK	5.0 <sup>(Note 4)</sup>	А
PROOUT Pin Output Current (Peak 10µs)	IPROOUTPEA	2.5 <sup>(Note 4)</sup>	А
FLT, RDY Pin Output Current	IFLT	10	mA
FET_G Pin Output Current (Peak 1µs)	IFET_GPEAK	1	А
Power Dissipation	Pd	1.12 <sup>(Note 5)</sup>	W
Operating Temperature Range	Topr	-40 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Junction Temperature	Tjmax	+150	°C

(Note 2) Relative to GND1 (Note 3) Relative to GND2

(Note 4) Should not exceed Pd and Tj=150°C

(Note 5) Derate above  $Ta=25^{\circ}C$  at a rate of 9.5mW/°C. Mounted on a glass epoxy of 70 mm × 70 mm × 1.6 mm **Caution:** Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

## **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
Main Power Supply Voltage <sup>(Note 6)</sup>	VBATT	4.0	32	V
Output-Side Positive Supply Voltage <sup>(Note 7)</sup>	V <sub>CC2</sub>	10	20	V
Output-Side Negative Supply Voltage <sup>(Note 7)</sup>	V <sub>EE2</sub>	-12	0	V
Maximum Difference Between Output-Side Positive and Negative Voltages	Vmax2	10	28	V
Switching frequency for switching controller	fswr	100	500	kHz

(Note 6) Relative to GND1 (Note 7) Relative to GND2

## Insulation Related Characteristics (UL1577)

Parameter	Symbol	Characteristic	Unit
Insulation Resistance (V <sub>IO</sub> =500V)	Rs	>10 <sup>9</sup>	Ω
Insulation Withstand Voltage / 1min	V <sub>ISO</sub>	2500	Vrms
Insulation Test Voltage / 1sec	Viso	3000	Vrms

## **Electrical Characteristics**

(Unless otherwise specified Ta=-40°C to +125°C, VBATT=4.0V to 32V, VCC2=UVLO to 20V, VEE2=-12V to 0V)

Unless otherwise specified Ta= Parameter	Symbol	Min	Тур	Max	Unit	Conditions
General						
Main Power Supply		1.1	1.6	2.1	A	
Circuit Current 1	I <sub>BATT1</sub>	1.1	1.0	2.1	mA	V_BATT=4.0V
Main Power Supply		0.0	1.3	1.0		V DATT 40.0V
Circuit Current 2	IBATT2	0.8	1.3	1.8	mA	V_BATT=12.0V
Main Power Supply		0.0	4.0	4.0		
Circuit Current 3	IBATT3	0.8	1.3	1.8	mA	V_BATT=32.0V
Output Side Circuit Current 1	Icc21	0.7	1.4	2.1	mA	Vcc2=14V, OUT1=L
Output Side Circuit Current 2	Icc22	0.4	1.1	1.8	mA	Vcc2=14V, OUT1=H
Output Side Circuit Current 3	Icc23	0.8	1.5	2.2	mA	Vcc2=18V, OUT1=L
Output Side Circuit Current 4	Icc24	0.8	1.2	1.9	mA	Vcc2=18V, OUT1=H
Output Side Circuit Current 5	Icc25	0.9	1.6	2.3	mA	V <sub>CC2</sub> =16V, V <sub>EE2</sub> =-8V, OUT1=L
Output Side Circuit Current 6	I <sub>CC26</sub>	0.6	1.3	2.0	mA	V <sub>CC2</sub> =16V, V <sub>EE2</sub> =-8V, OUT1=H
Switching Power Supply Control	er					
						4.2V <v_batt≤32v< td=""></v_batt≤32v<>
FET_G Output Voltage H1	Vfetgh1	3.8	4.0	4.2	V	I <sub>FET_G</sub> =0A(open)
						V_BATT ≤ 4.2V
FET_G Output Voltage H2	Vfetgh2	-	V_BATT-0.2	V_BATT	V	I <sub>FET_G</sub> =0A(open)
FET_G Output Voltage L	V <sub>FETGL</sub>	0	-	0.3	V	I <sub>FET_G</sub> =0A(open)
FET_G ON-Resistance					_	
(Source-side)	Rongh	3	6	12	Ω	10mA
FET_G ON-Resistance	_				-	
(Sink-side)	Rongl	0.3	0.6	1.3	Ω	10mA
Oscillation Frequency	fsw	182	200	222	kHz	RT=68kΩ
Soft-start Time	tss	-	-	50	ms	
FB Pin Threshold Voltage	VFB	1.47	1.50	1.53	V	
FB Pin Input Current	IFB	-0.8	0	0.8	μA	
COMP Pin Sink Current	ICOMPSINK	-160	-80	-40	μA	
COMP Pin Source Current		40	80	160	μA	
V_BATT UVLO ON Voltage	VUVLOBATTL	3.20	3.40	3.60	V	
V_BATT UVLO Hysteresis	VUVLOBATTHYS	0.07	0.1	0.13	V	
Maximum ON DUTY	DONMAX	-	48	-	%	
Over Voltage Detection Threshold	Vovth	1.60	1.65	1.70	V	
Under Voltage Detection Threshold	Vuvth	1.23	1.30	1.37	V	
Over-Current Detection Threshold	Vостн	0.17	0.20	0.23	V	
Protection Holding Time	t <sub>DCDCRLS</sub>	20	40	60	ms	
Logic Block						•
Logic High Level Input Voltage	VINH	2.0	-	5.5	V	INA, INB, ENA
Logic Low Level Input Voltage	VINL	0	-	0.8	V	INA, INB, ENA
Logic Pull-Down Resistance	RIND	25	50	100	kΩ	INA, INB, ENA
Logic Input Filtering Time	t <sub>INFIL</sub>	-	-	90	ns	INA, INB
ENA Input Filtering Time	t <sub>ENAFIL</sub>	-	0.5	0.8	μs	ENA
MODE Low Level Input Voltage	VMODEL	0	-	0.3×V <sub>CC2</sub>	V	MODE, relative to GND2
MODE High Level Input Voltage	V <sub>MODEH</sub>	0.7×V <sub>CC2</sub>	-	V <sub>CC2</sub>	V	MODE, relative to GND2

## **Electrical Characteristics – continued**

(Unless otherwise specified Ta=-40°C to +125°C, VBATT=4.0V to 32V, VCC2=UVLO to 20V, VEE2=-12V to 0V)
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Symbol RONH RONL IOUT1MAX RONPRO tPONA tPONB tPOFFA tPOFFB	Min 0.50 0.25 3.0 0.45 45 50 40	Typ 0.85 0.45 4.5 0.85 75 80	Max 1.45 0.80 - 1.55 105	Unit Ω Ω Α	Conditions I <sub>OUT1H</sub> =40mA I <sub>OUT1L</sub> =40mA V <sub>CC2</sub> =15V Design assurance
RONL IOUT1MAX RONPRO tPONA tPONB tPOFFA tPOFFB	0.25 3.0 0.45 45 50	0.45 4.5 0.85 75	0.80 - 1.55	Ω A	I <sub>OUT1L</sub> =40mA V <sub>CC2</sub> =15V
RONL IOUT1MAX RONPRO tPONA tPONB tPOFFA tPOFFB	0.25 3.0 0.45 45 50	0.45 4.5 0.85 75	0.80 - 1.55	Ω A	I <sub>OUT1L</sub> =40mA V <sub>CC2</sub> =15V
IOUT1MAX RONPRO tPONA tPONB tPOFFA tPOFFB	3.0 0.45 45 50	4.5 0.85 75	- 1.55	А	V <sub>CC2</sub> =15V
Ronpro tpona tponb tpoffa tpoffb	0.45 45 50	0.85 75			
tpona tponb tpoffa tpoffb	45 50	75		Ω	
tponb tpoffa tpoffb	50		105		Iproout=40mA
tpoffa tpoffb		80	100	ns	INA=PWM, INB=L
<b>t</b> POFFB	40		110	ns	INA=H, INB=PWM
		70	100	ns	INA=PWM, INB=L
	35	65	95	ns	INA=H, INB=PWM
<b>t</b> pdista	-25	-5	15	ns	t <sub>POFFA</sub> — t <sub>PONA</sub>
<b>t</b> PDISTB	-35	-15	5	ns	tроffb — tponb
t <sub>RISE</sub>	-	50	-	ns	10nF between OUT1-VEE2
tFALL	-	50	-	ns	Design assurance
R <sub>ON2</sub>	0.25	0.45	0.80	Ω	I <sub>OUT2</sub> =40mA
Vout20N	1.8	2	2.2	V	Relative to VEE2
СМ	100	-	-	kV/µs	Design assurance
N/	0.05	0.00	0.05		
VUVLOINL	0.85	0.90	0.95	V	UVLOIN, MODE=L
\ <i>\</i>	0.10×	0.11×	0.12×		
VUVLOINHYS	VUVLOINL	VUVLOINL	VUVLOINL	V	UVLOIN, MODE=L
Vuvlo2l	10.9	11.5	12.1	V	VCC2, MODE=H
V <sub>UVLO2HYS</sub>	0.8	1.2	1.6	V	VCC2, MODE=H
tuvlo2fil	0.25	1.5	3.7	μs	
<b>t</b> DESATleb	0.14	0.20	0.26	μs	Design assurance
VSCDET	0.47	0.50	0.53	V	Relative to GND2
tscpfil	0.12	0.2	0.28	μs	
t <sub>SCPPRO</sub>	0.26	0.38	0.50	μs	
Vectini	_	0.1	0.22	V	Iscpin=1mA
		0.1	0.22	v	
<b>t</b> PROFLT	0.1	0.4	0.7	μs	
VISDET	1.61	1.70	1,79	V	Relative to GND2
		-			
	-	0.18			I <sub>FLT</sub> =5mA
*1616					
Vosfbh	4.5	5.0	5.5	V	Relative to GND2
VOSFBL	4.0	4.5	5.0	V	Relative to GND2
tosfbfil	1.5	2.0	2.5	us	
	-				I <sub>RDY</sub> =5mA
	trise tfall Ron2 Vout20N CM VUVLOINL VUVLOINHYS VUVLO2L VUVLO2HVS tUVLO2FIL tDESATIeb VSCDET tSCPFIL tSCPFIL tSCPFIL tSCPFIL VSCPINL tPROFLT VTSDET tTSFIL tSTO VFLTL VOSFBH	trise       -         tfall       -         RON2       0.25         VOUT2ON       1.8         CM       100         VUVLOINL       0.85         VUVLOINHYS       0.10x         VUVLOINHYS       0.10x         VUVLOINHYS       0.10x         VUVLOZL       10.9         VUVLO2HYS       0.8         tuvlo2FIL       0.25         tdesatieb       0.14         VSCDET       0.47         tSCPPRO       0.26         VSCPINL       -         tproflt       0.12         tscpfil       0.11         VTSDET       1.61         ttsfil       4         tsto       30         VFLTL       -         VOSFBH       4.5         VOSFBL       4.0         tosfbfil       1.5	trise         -         50           tfall         -         50           RON2         0.25         0.45           Voutzon         1.8         2           CM         100         -           Vuvloinl         0.85         0.90           Vuvloinl         0.10×         0.11×           VuvlozHYS         0.8         1.2           tuvlozHYS         0.14         0.20           VscPFIL         0.12         0.2           tscPFIL         0.1         0.4           V	trise         -         50         -           tfall         -         50         -           RON2         0.25         0.45         0.80           Voutzon         1.8         2         2.2           CM         100         -         -           VuvLOINL         0.85         0.90         0.95           VuvLOINL         0.10x         0.11x         0.12x           VuvLOINL         0.109         11.5         12.1           VuvLO2L         10.9         11.5         12.1           VuvLO2HYS         0.8         1.2         1.6           tuvLO2FIL         0.25         1.5         3.7           tbESATIED         0.14         0.20         0.26           Vscdet         0.47         0.50         0.53           tscPFIL         0.12         0.2         0.28           tscPPRO         0.26         0.38         0.50           Vscdet         -         0.1         0.22           tscPPRO         0.26         0.38         0.50           Vscpint         -         0.1         0.22           tscopfLt         0.1         0.4         0.7	trise         -         50         -         ns           tFALL         -         50         -         ns           RON2         0.25         0.45         0.80         Ω           VOUT2ON         1.8         2         2.2         V           CM         100         -         -         kV/μs           VUVLOINL         0.85         0.90         0.95         V           VUVLOINL         0.85         11x         0.12x         V           VUVLOZL         10.9         11.5         12.1         V           VUVLOZL         10.9         11.5         12.1         V           VUVLOZHYS         0.8         1.2         1.6         V           VUVLOZH         0.25         1.5         3.7         μs           tbESATIeb         0.14         0.20         0.26         μs           VSCDET         0.47         0.50         0.53         V

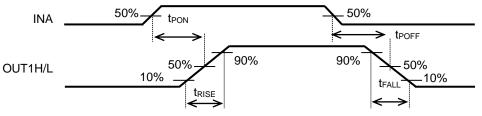


Figure 2. INA-OUT1H/L Timing Chart

## UL1577 Ratings Table

Following values are described in UL Report.

Parameter	Values	Units	Conditions
Side 1 (Input Side) Circuit Current	1.3	mA	V_BATT=12V, OUT1H/L=L
Side 2 (Output Side) Circuit Current	1.6	mA	VCC2=18V, VEE2=-6V, OUT1H/L=L
Side 1 (Input Side) Consumption Power	15.6	mW	V_BATT=12V, OUT1H/L=L
Side 2 (Output Side) Consumption Power	38.4	mW	VCC2=18V, VEE2=-6V, OUT1H/L=L
Isolation Voltage	2500	Vrms	
Maximum Operating (Ambient) Temperature	125	°C	
Maximum Junction Temperature	150	°C	
Maximum Strage Temperature	150	°C	
Maximum Data Transmission Rate	5.5	MHz	

## **Typical Performance Curves**

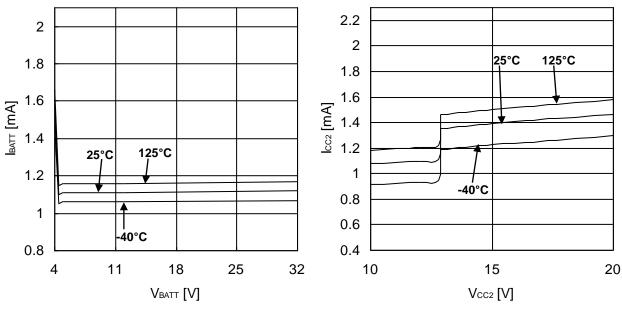


Figure 3. Main Power Supply Circuit Current

Figure 4. Output Side Circuit Current (MODE=H, VEE2=0V, OUT1=L)

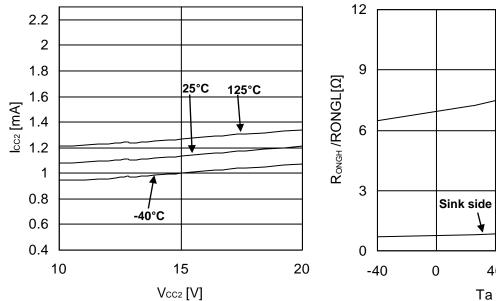


Figure 5. Output Side Circuit Current (MODE=H, VEE2=0V, OUT1=H)

Source side 40 80 120 Ta [°C]

Figure 6. FET\_G ON-Resistance (Source side/Sink side)

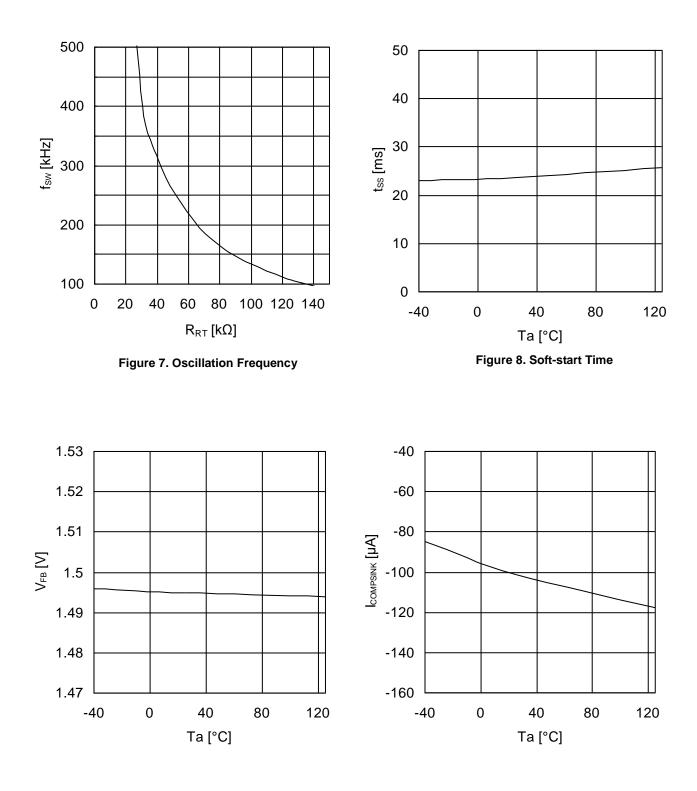
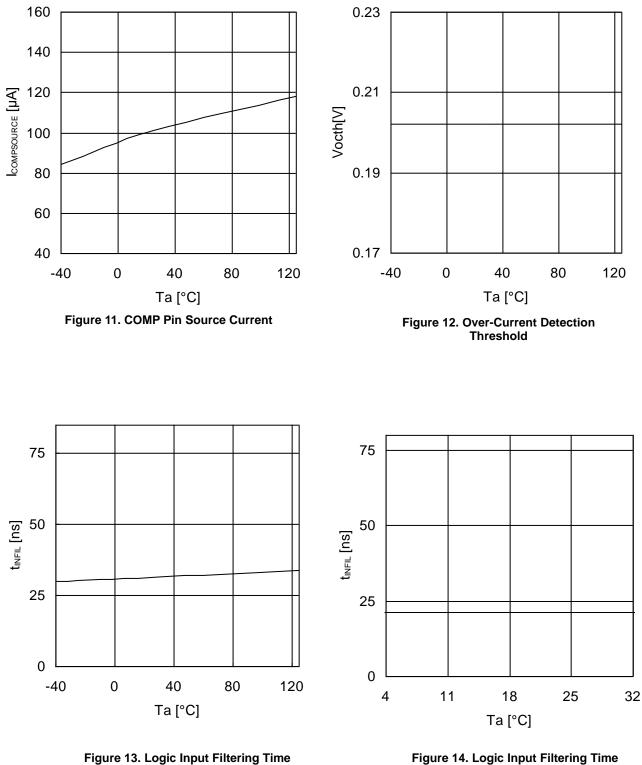


Figure 9. FB Pin Threshold Voltage

Figure 10. COMP Pin Sink Current



(L pulse)

Figure 14. Logic Input Filtering Time (H pulse)

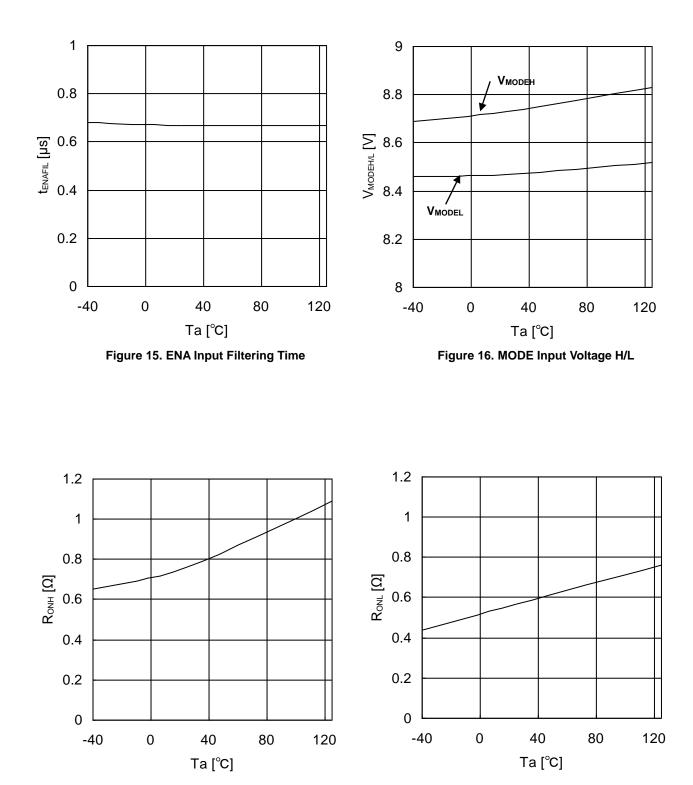


Figure 17. OUT1H ON-Resistance (Iout1=40mA)

Figure 18. OUT1L ON-Resistance (Iout1=40mA)

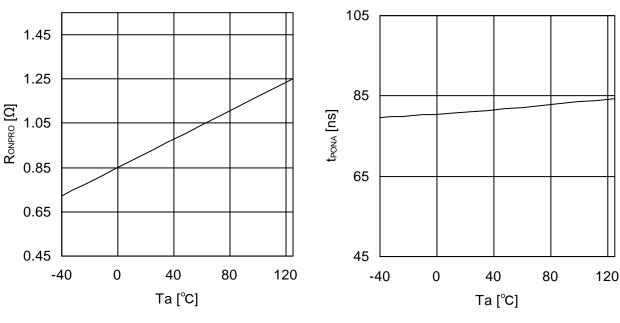
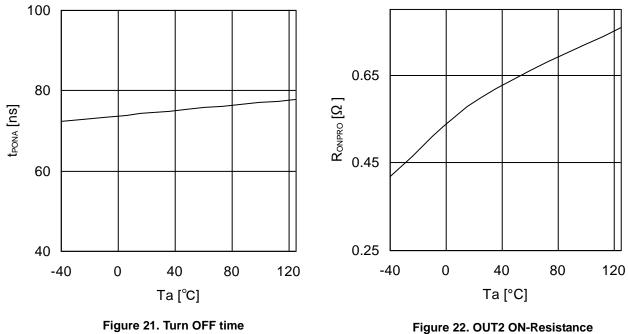


Figure 19. PROOUT ON-Resistance (IPROOUT=40mA)

Figure 20. Turn ON time



(I<sub>OUT2</sub>=40mA)

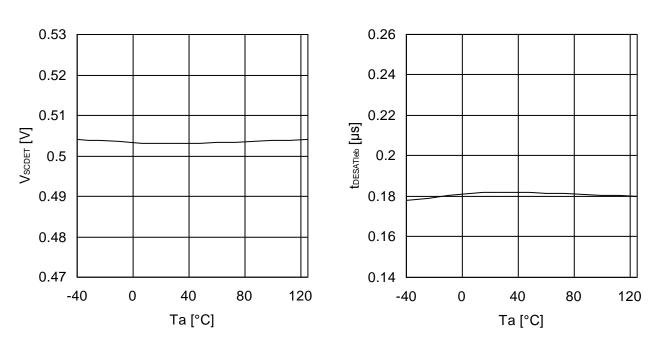
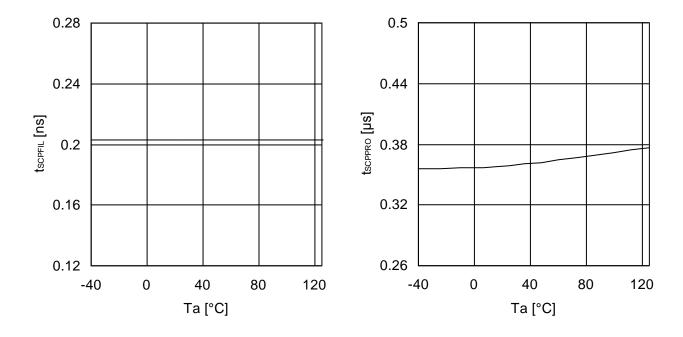
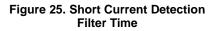
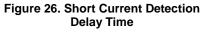


Figure 23. Short Current Detection Voltage

Figure 24. DESAT Leading Edge Blanking Time







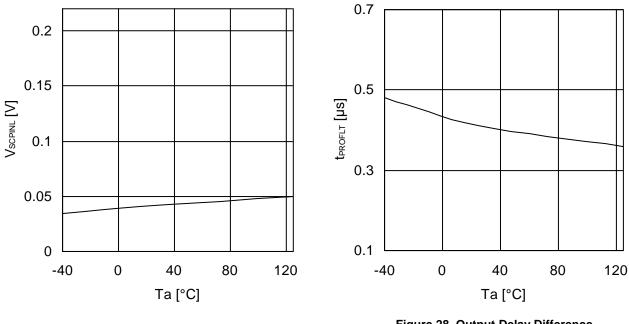


Figure 27. SCPIN Pin Low Voltage

Figure 28. Output Delay Difference between PROOUT and FLT

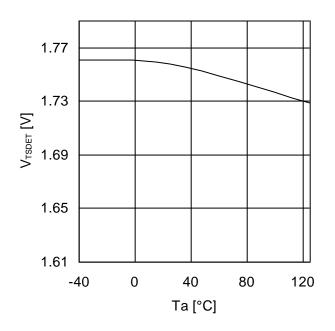


Figure 29. Thermal Detection Voltage

## **Application Information**

- 1. Description of Pins and Cautions on Layout of Board
  - (1) V\_BATT (Main Power Supply Pin) This is the main power supply pin. Connect a bypass capacitor between V\_BATT and GND1 in order to suppress voltage variations.
  - (2) GND1 (Input-side Ground Pin) The GND1 pin is a ground pin on the input side.
  - (3) VCC2 (Output-side Positive Power Supply Pin) The VCC2 pin is a positive power supply pin on the output side. To reduce voltage fluctuations due to OUT1H/L pin output current and due to the driving current of the internal transformers, connect a bypass capacitor between VCC2 and GND2 pins.
  - (4) VEE2 (Output-side Negative Power Supply Pin) The VEE2 pin is a power supply pin on the output side. To suppress voltage fluctuations due to OUT1H/L pin output current and due to the driving current of the internal transformers, connect a bypass capacitor between the VEE2 and the GND2 pins. Connect the VEE2 pin to the GND2 pin when no negative power supply is used,
  - (5) GND2 (Output-side Ground Pin) The GND2 pin is a ground pin on the output side. Connect the GND2 pin to the emitter / source of a power device.

#### (6) INA, INB, ENA (Control Input Terminal)

The INA, INB, ENA are pins used to determine output logic.

ENA	INB	INA	OUT1H	OUT1L
L	Х	Х	Hi-Z	L
Н	Н	Х	Hi-Z	L
Н	L	L	Hi-Z	L
Н	L	Н	Н	Hi-Z

Fault state(FLT=L output) is released in rising of ENA(L $\rightarrow$  H).

#### (7) FLT (Fault Output Pin)

The FLT pin is an open drain pin used to output a fault signal when short circuit protection function (SCP) or thermal protection function is activated, and will be cleared at the rising edge of ENA.

Status	FLT
While in normal operation	Hi-Z
When a fault occurs (When SCP or thermal protection is activated)	L

#### (8) RDY (Ready Output Pin)

The RDY pin shows the status of three internal protection features which are V\_BATT UVLO, VCC2 UVLO, and output state feedback (OSFB). The term 'output state feedback' shows whether PROOUT pin voltage (High or Low) corresponds to input logic or not.

Status	RDY
While in normal operation	Hi-Z
V_BATT UVLO or VCC2 UVLO or Output state feedback	L

#### (9) MODE (Mode Selection Pin of Output-side UVLO)

The MODE pin is a pin which selects internal threshold or external setting threshold for output-side UVLO.

MODE	Output-side UVLO threshold voltage
L (=GND2)	Setting by external. (Use UVLOIN pin)
H (=VCC2)	Fixed (=VUVLO2L). (Connect UVLOIN pin to VCC2 pin)

(10) UVLOIN (Output-side UVLO Setting Input Pin)

The UVLOIN pin is a pin for deciding UVLO setting value of VCC2. The threshold value of UVLO can be set by dividing the resistance voltage of VCC2 and inputting such value. UVLOIN activates only at MODE pin=L. When MODE pin=H, connect UVLOIN pin to VCC2 pin.

## (11) OUT1H, OUT1L(Output Pin)

The OUT1H pin is a source side pin used to drive the gate of a power device, and the OUT1L pin is a sink side pin used to drive the gate of a power device.

(12) OUT2 (Miller Clamp Pin)

This is the miller clamp pin for preventing a rise of gate voltage due to miller current of output element connected to OUT1. It also functions as a pin for monitoring gate voltage for miller clamp and OUT2 pin voltage become not more than VOUT2ON(typ 2.0V), miller clamp function operates. OUT2 should be connect to VEE2 when miller clamp function is not used.

(13) PROOUT (Soft Turn-OFF Pin)

This is a pin for soft turn-OFF of output pin when short-circuit protection is in action. It also functions as a pin for monitoring gate voltage for output state feedback function.

(14) SCPIN(Short Circuit Current Detection Pin)

The SCPIN pin is a pin used to detect current for short circuit protection. When the SCPIN pin voltage exceeds  $V_{SCDET}$ , SCP function will be activated. This may cause the IC to malfunction in an open state. To avoid such trouble, short-circuit the SCPIN pin to the GND2 pin when the short circuit protection is not used. In order to prevent the wrong detection due to noise, the noise filter time t<sub>SCPFIL</sub> is set.

(15) VTSIN (Thermal Detection Pin)

The VTSIN pin is a temperature sensor voltage input pin, which can be used for thermal protection of an output device. If VTSIN pin voltage becomes  $V_{TSDET}$  or less, OUT1H/L pin is set to HiZ/L. IC may malfunction in the open status, so be sure to supply the VTSPIN more than  $V_{TSDET}$  if the thermal protection function is not used. In order to prevent the wrong detection due to noise, the noise mask time  $t_{TSMSK}$  is set. In addition, it can be used also as compulsive shutdown terminal other than a temperature sense by inputting a comparator output etc.

(16) RT (Switching Frequency Setting Pin for Switching Controller)

The RT pin is a pin used to make setting of switching frequency of switching controller. The switching frequency is determined by the resistance value connected between RT and GND1. The value of switching frequency is determined by the value of the resistor  $R_{RT}$ .

$$F_{SW}[kHz] = 1/(7.3 \times 10^{-8} \times R_{RT} + 2.2 \times 10^{-4})$$

(17) FB (Error Amplifier Inverting Input Pin for Switching Controller)

This is a voltage feedback pin of the switching controller. This pin combine with voltage monitoring at overvoltage protection function for switching controller. When overvoltage or under voltage protection is activated, switching controller will be at OFF state (FET\_G pin outputs Low). When the protection holding time (t<sub>DCDCRLS</sub>) is completed, the protection function will be released. Under voltage function is not activated during soft-start.

- (18) COMP (Error Amplifier Output Pin for Switching Controller)
   This is the gain control pin of the switching controller. Connect a phase compensation capacitor and resistor.
- (19) VREG (Input-side internal power supply pin) This is the input-side internal power supply pin. Be sure to connect a capacitor between VREG and GND1 even when the switching controller is not used, in order to prevent oscillation and suppress voltage variation due to FET\_G output current.
- (20) FET\_G (MOS FET Control Pin for Switching Controller) This is a MOSFET control pin for the switching controller transformer drive.
- (21) SENSE (Connection to the Current Feedback Resistor of the Switching Controller) This is a pin connected to the resistor of the switching controller current feedback. This pin combines with current monitoring at overcurrent protection function for switching controller. When overcurrent protection is activated, switching controller will be at OFF state (FET\_G pin outputs Low). When the protection holding time (t<sub>DCDCRLS</sub>) is completed, the over-current function will be released.

## 2. Description of Functions and Examples of Constant Setting

## (1) Miller Clamp Function

When OUT1=L and OUT2 pin voltage < V<sub>OUT2ON</sub>, internal MOS of OUT2 pin is turned ON and miller clamp function operates.

IN	OUT2 pin input voltage	OUT2
L	Not more than V <sub>OUT2ON</sub>	L
Н	Х	Hi-Z

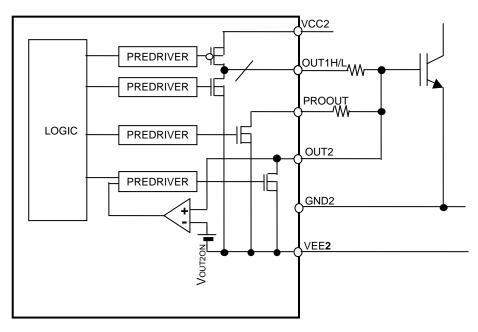
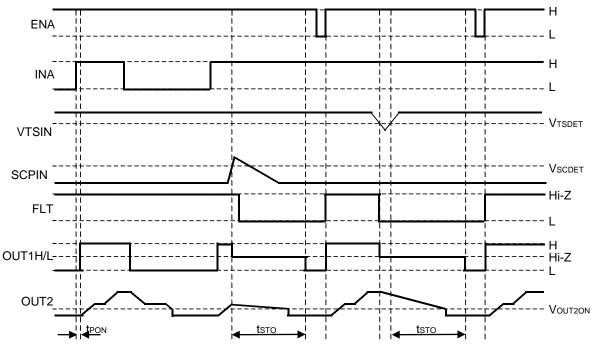
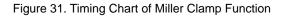


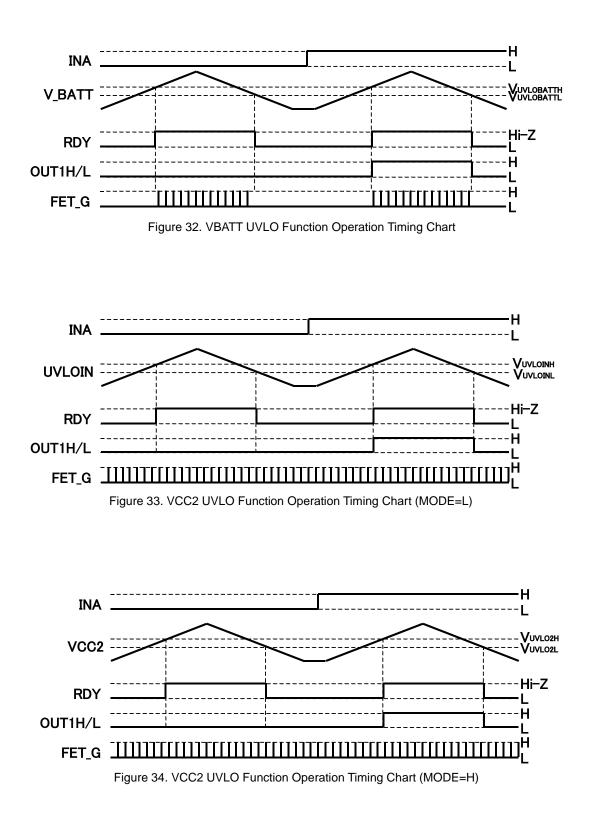
Figure 30. Block Diagram of Miller Clamp Function





(2) Under Voltage Lockout (UVLO) Function

The BM60054FV-C incorporates the under voltage lockout (UVLO) function on V\_BATT and VCC2. When the power supply voltage drops to the UVLO ON voltage, the OUT1H/L pin will output the "Hi-Z / L" and the FLT pin will output the "L" signal. When the power supply voltage rises to the UVLO OFF voltage, these pins will be reset. In addition, to prevent mis-triggers due to noise, mask time tuvLOBATTFIL and tuvLO2FIL are set on both voltage sides.



## BM60054FV-C

(3) Short Circuit Protection Function (SCP)

When the SCPIN pin voltage exceeds  $V_{SCDET}$ , the SCP function will be activated. When the SCP function is activated, the OUT1H/L pin voltage will be set to the "Hi-Z/Hi-Z" level and the PROOUT pin voltage will go to the "L" level first (soft turn-OFF). Next, After t<sub>STO</sub> has passed, OUT1H/L pin become Hi-Z/L (PROOUT pin hold L). In addition, when OUT2 pin voltage < V<sub>OUT2ON</sub>, miller clamp function operates.

When the rising edge is put in the ENA pin, the SCP function will be released.

When OUT1H/L=Hi-Z/L or Hi-Z/Hi-Z, internal MOSFET connected to SCPIN pin turns ON to discharge C<sub>BLANK</sub> for desaturation protection function. When OUT1H/L=H/Hi-Z, internal MOSFET connected to SCPIN pin turns OFF.

$$V_{DESAT}[V] = V_{SCDET} \bullet \frac{R3 + R2}{R3} - V_{F_{D1}}$$

$$V_{CC2_{MIN}}[V] > V_{SCDET} \bullet \frac{R3 + R2 + R1}{R3}$$

$$t_{BLANKoutemal}[s] = -\frac{R2 + R1}{R3 + R2 + R1} \bullet R3 \bullet C_{BLANK} \bullet \ln(1 - \frac{R3 + R2 + R1}{R3} \bullet \frac{V_{SCDET}}{V_{CC2}}) + t_{DESATIlet}$$

		設定参考値	
Vdesat	R1	R2	R3
4.0V	15 kΩ	39kΩ	4.7kΩ
4.5V	15 kΩ	47kΩ	5.1kΩ
5.0V	15 kΩ	51kΩ	5.1kΩ
5.5V	15 kΩ	27kΩ	2.4kΩ
6.0V	15 kΩ	33kΩ	2.7kΩ
6.5V	15 kΩ	62kΩ	4.7kΩ
7.0V	15 kΩ	47kΩ	3.3kΩ
7.5V	15 kΩ	20kΩ	1.3kΩ
8.0V	15 kΩ	82kΩ	5.1kΩ
8.5V	15 kΩ	62kΩ	3.6kΩ
9.0V	15 kΩ	33kΩ	1.8kΩ
9.5V	15 kΩ	75kΩ	3.9kΩ
10.0V	15 kΩ	68kΩ	3.3kΩ

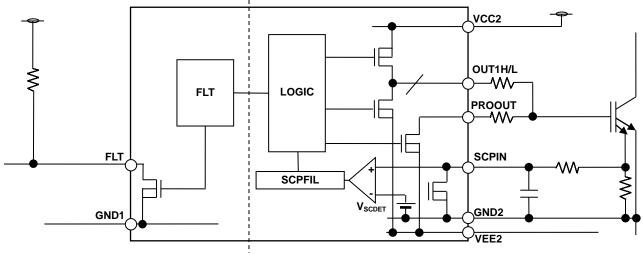


Figure 35. Block Diagram of Short Circuit Protection

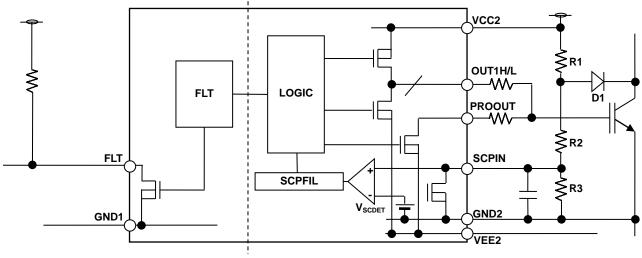
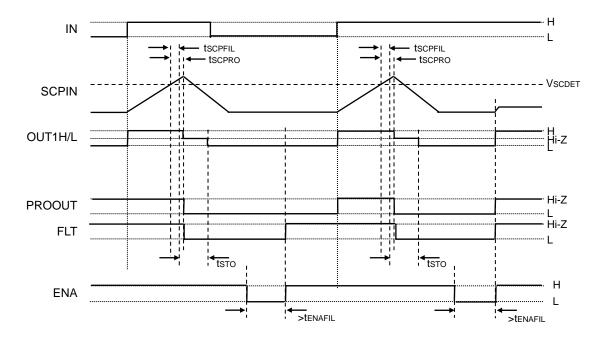
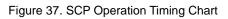


Figure 36. Block Diagram of DESAT





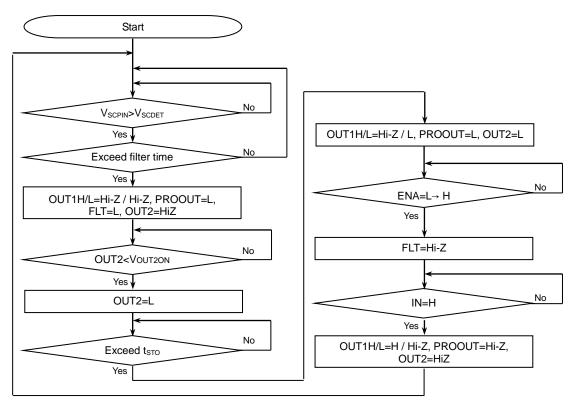


Figure 38. SCP Operation Status Transition Diagram

(4) Thermal Protection Function

When the VTSIN pin voltage becomes  $V_{TSDET}$  or less, the thermal protection function will be activated. When the thermal protection function is activated, the OUT1H/L pin voltage will be set to the "Hi-Z/Hi-Z" level and the PROOUT pin voltage will go to the "L" level first (soft turn-OFF). Next, when the VTSIN pin voltage rises to the threshold value and after t<sub>STO</sub> has passed, OUT1H/L pin become Hi-Z/L (PROOUT pin hold L). In addition, when OUT2 pin voltage < V<sub>OUT2ON</sub>, miller clamp function operates.

When the rising edge is put in the ENA pin, the thermal protection function will be released.

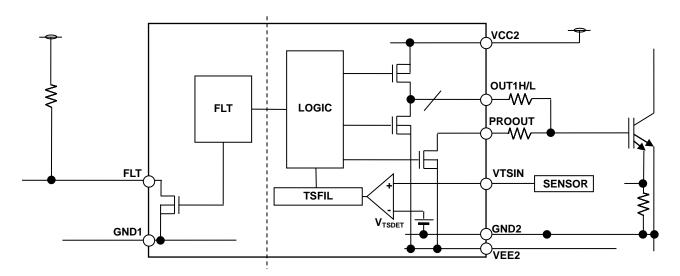


Figure 39. Block Diagram of thermal protection function

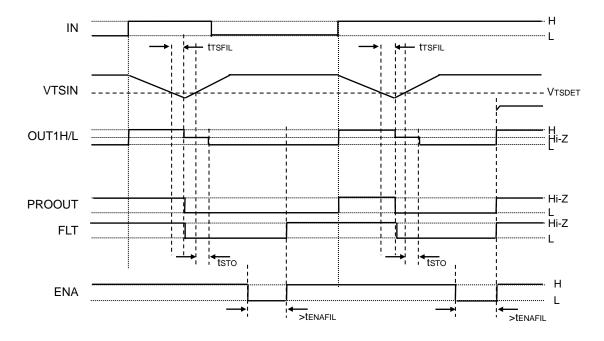


Figure 40. Thermal Protection Function Operation Timing Chart

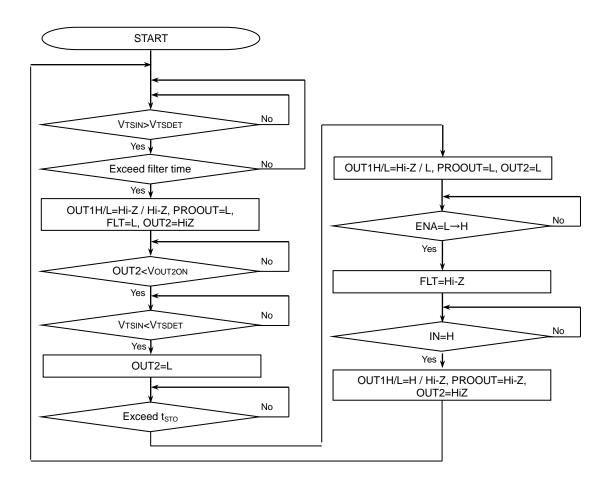


Figure 41. Thermal Protection Function Operation Status Transition Diagram

#### (5) Switching Controller

#### (a) Basic action

This IC has a built-in switching power supply controller which repeats ON/OFF synchronizing with internal clock set by RT pin. When VBATT voltage is supplied (VBATT >  $V_{UVLOBATTH}$ ), FET\_G pin starts switching by soft-start. Output voltage is determined by the following equation by external resistance and winding ratio "n" of flyback transformer (n=  $V_{OUT2}$  side winding number/ $V_{OUT1}$  side winding number)

$$V_{OUT2} = V_{FB} \times \{ (R_1 + R_2) / R_2 \} \times n [V]$$

(b) MAX DUTY

When, for example, output load is large, and voltage level of SENSE pin does not reach current detection level, output is forcibly turned OFF by Maximum On Duty (DONMAX).

(c) Protection function

The switching controller has protection function as overvoltage protection (OVP), under voltage protection (UVP), and over-current protection (OCP). OVP and UVP monitor the voltage of FB pin, OCP monitor the voltage of SENSE pin.

When the protection function is activated, switching controller will be OFF state (FET\_G pin outputs Low). The protection holding time (t<sub>DCDCRLS</sub>) is completed, the protection function will be released. Under voltage function is not activated during soft-start.

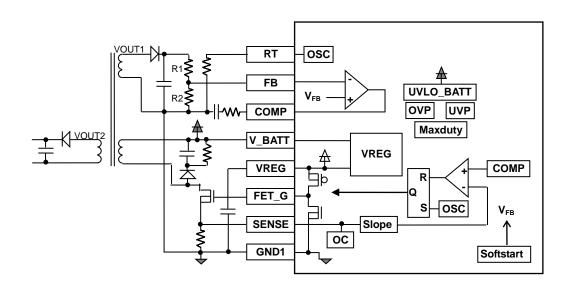


Figure 42. Block Diagram of switching controller

(d)The pin handling when not using switching controller

When not using switching controller, please do pin handling as follows.

pin no.	pin name	processing method
21	RT	pull down in gnd1 by 68k $\Omega$
22	FB	connect to VREG
23	COMP	connect to VREG
24	V_BATT	connect power supply
25	VREG	connect capacitor
26	FET_G	open
27	SENSE	connect to VREG

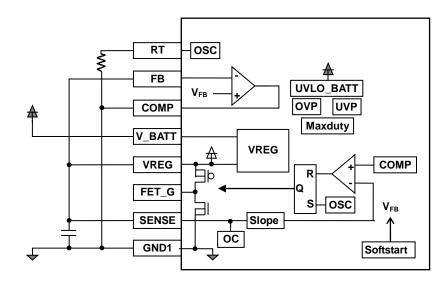


Figure 43. The pin handling when not using switching controller

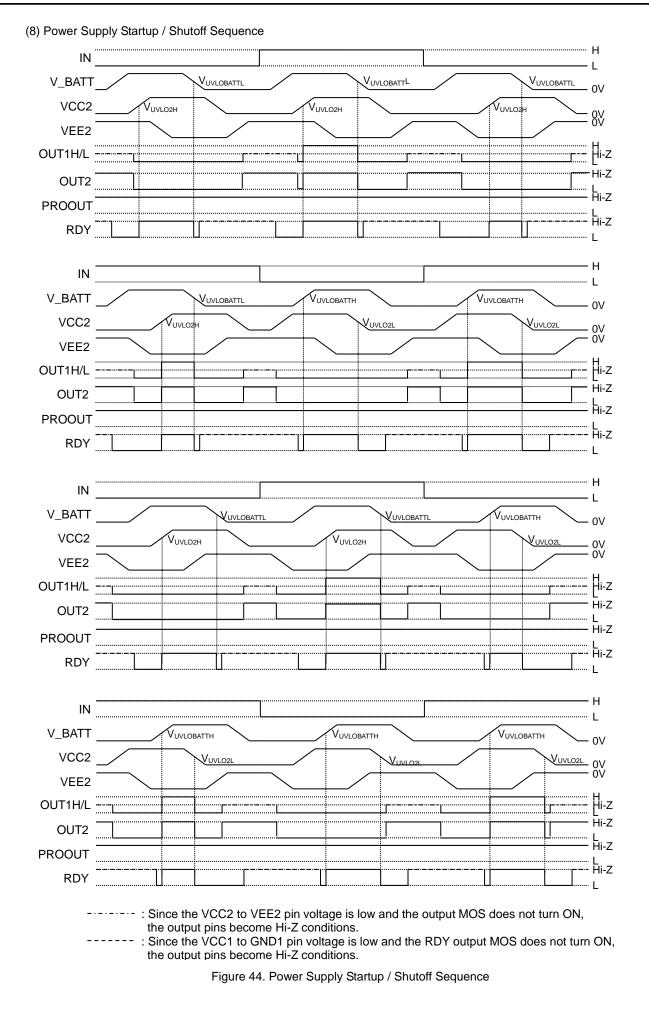
(6) Gate State Monitoring Function

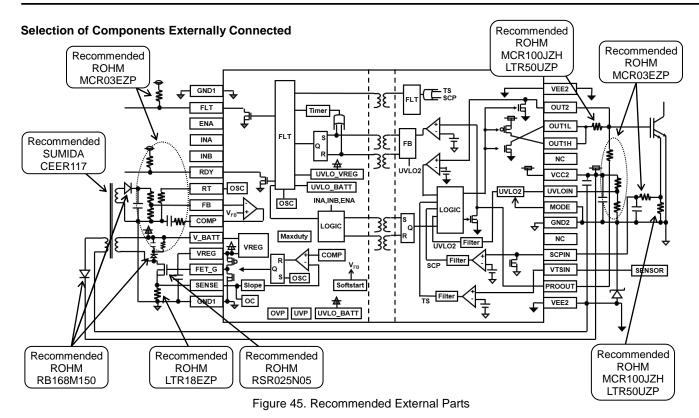
When gate logic and input logic of output device monitored with PROOUT pin are compared, a logic L is output from RDY pin when they disaccord. In order to prevent the detection error due to delay of input and output, OSFB filter time t<sub>OSFBFIL</sub> is provided.

#### (7) I/O Condition Table

			Input						Output							
No.	Status	V B A T T	V C C 2	S C P I N	> H S - N	E N A	I N B	I N A	O U T 2	P R O O U T	O U T H	O U T 1 L	O U T 2	P R O O U T	F L T	R D Y
1	SCP	0	0	Н	Н	Н	L	Н	н	Х	Hi-Z	Hi-Z	Hi-Z	L	L	Hi-Z
2	3CP	0	0	Н	Н	Н	L	Н	L	Х	Hi-Z	Hi-Z	L	L	L	Hi-Z
3	UVLO_VBATT	UVLO	0	L	Н	Х	Х	Х	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
4	UVEO_VBATT	UVLO	0	L	Н	Х	Х	Х	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	L
5	UVLO_VCC2	0	UVLO	L	Н	Х	Х	Х	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
6	0010_0002	0	UVLO	L	Н	Х	Х	Х	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	L
7	Thermal	0	0	L	L	Х	Х	Х	Н	Х	Hi-Z	Hi-Z	Hi-Z	L	L	Hi-Z
8	protection	0	0	L	L	Х	Х	Х	L	Х	Hi-Z	Hi-Z	L	L	L	Hi-Z
9	Disable	0	0	L	Н	L	Х	Х	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
10	Disable	0	0	L	Н	L	Х	Х	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
11	INB active	0	0	L	Н	Н	Н	Х	Н	Н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
12	IND active	0	0	L	Н	Н	Н	Х	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
13	Normal Operation	0	0	L	Н	Н	L	L	Н	н	Hi-Z	L	Hi-Z	Hi-Z	Hi-Z	L
14	I Immunt	0	0	L	Н	Н	L	L	L	L	Hi-Z	L	L	Hi-Z	Hi-Z	Hi-Z
15	Normal Operation	0	0	L	Н	Н	L	Н	Н	Н	Н	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z
16	البي من ما ا	0	0	L	Н	Н	L	Н	L	L	Н	Hi-Z	Hi-Z	Hi-Z	Hi-Z	L

○ : > UVLO, X:Don't care





## **Power Dissipation**

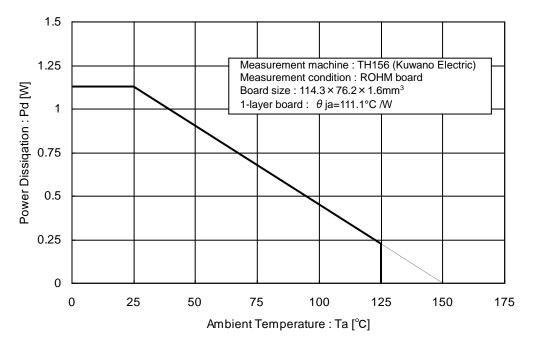


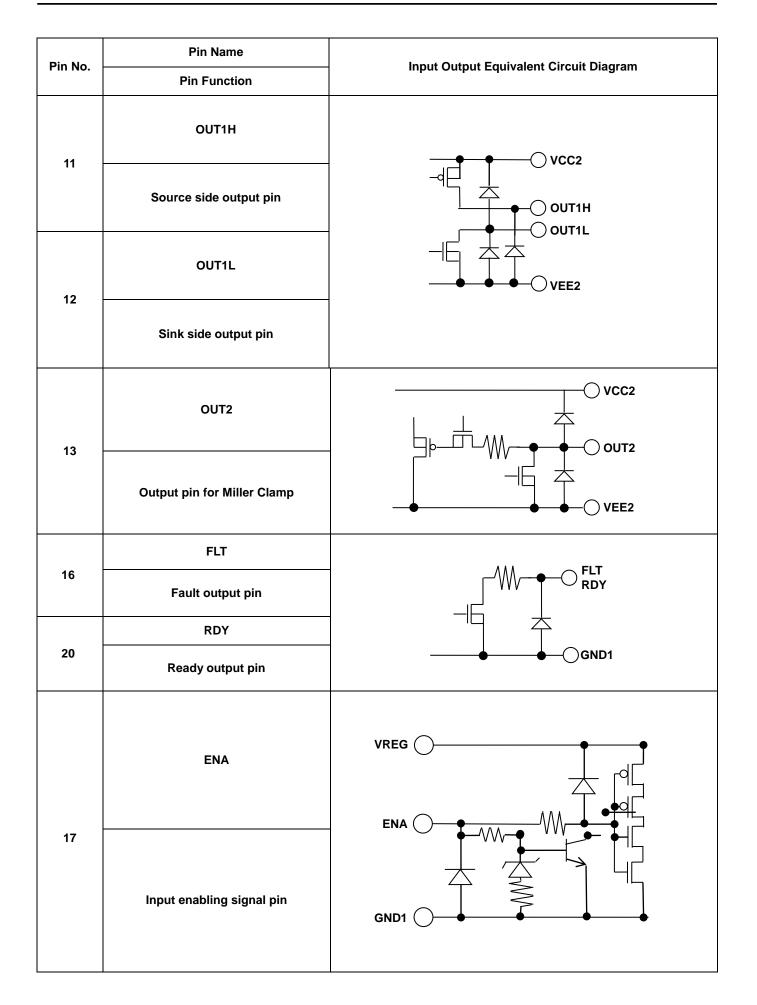
Figure 46. SSOP-B28W Derating Curve

#### **Thermal Design**

Please make sure that the IC's chip temperature Tj is not over 150°C, while considering the IC's power consumption (W), package power (Pd) and ambient temperature (Ta). When Tj=150°C is exceeded, the IC may malfunctions or some problems (ex. abnormal operation of various parasitic elements and increasing of leak current) may occur. Constant use under these circumstances leads to deterioration and eventually IC may destruct. Tjmax=150°C must be strictly obeyed under all circumstances.

## I/O Equivalence Circuits

	lence Circuits Pin Name	
Pin No.	Pin Function	Input Output Equivalent Circuit Diagram
2	PROOUT	
L	Soft turn-off pin / Gate voltage input pin	
3	VTSIN	
5	Thermal detection pin	
4	SCPIN	
	Schort circuit current detection pin	
7	MODE	
	Mode selection pin of output-side UVLO	GND2
	UVLOIN	
8	Output-side UVLO setting pin	



Pin No.	Pin Name	Input Output Equivalent Circuit Diagram
F 111 NO.	Pin Function	Input Output Equivalent Circuit Diagram
18	INA	
	Control input pin A	
	INB	
19	Control input pin B	
21	RT	
	Switching frequency setting pin for switching controller	
22	FB	V_BATT
22	Error amplifier inverting input pin for switching controller	

Pin No.	Pin Name	Innut Output Equivalent Circuit Diagram
Pin No.	Pin Function	Input Output Equivalent Circuit Diagram
23	СОМР	V_BATT Internal power supply COMP
23	Error amplifier output pin for switching controller	
25	VREG	Internal power
23	Input-side internal power supply pin	
	FET_G	
26	MOS FET control pin for switching controller	
	SENSE	V_BATT
27	Current detection pin for switching controller	

## **Operational Notes**

1. Reverse Connection of Power Supply

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Thermal Consideration

Should by any chance the power dissipation rating be exceeded, the rise in temperature of the chip may result in deterioration of the properties of the chip. The absolute maximum rating of the Pd stated in this specification is when the IC is mounted on a 70mm x 1.6mm glass epoxy board. In case of exceeding this absolute maximum rating, increase the board size and copper area to prevent exceeding the Pd rating.

6. Recommended Operating Conditions

These conditions represent a range within which the expected characteristics of the IC can be approximately obtained. The electrical characteristics are guaranteed under the conditions of each parameter.

7. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

- 8. Operation Under Strong Electromagnetic Field Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.
- 9. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

10. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

11. Unused Input Terminals

Input terminals of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input terminals should be connected to the power supply or ground line.

#### **Operational Notes – continued**

12. Regarding Input Pins of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

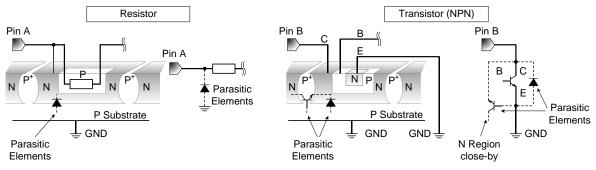
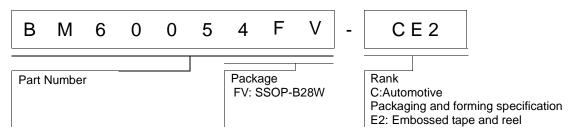


Figure 47. Example of Monolithic IC Structure

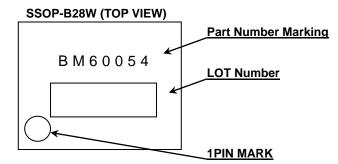
#### 13. Ceramic Capacitor

When using a ceramic capacitor, determine the dielectric constant considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

#### **Ordering Information**

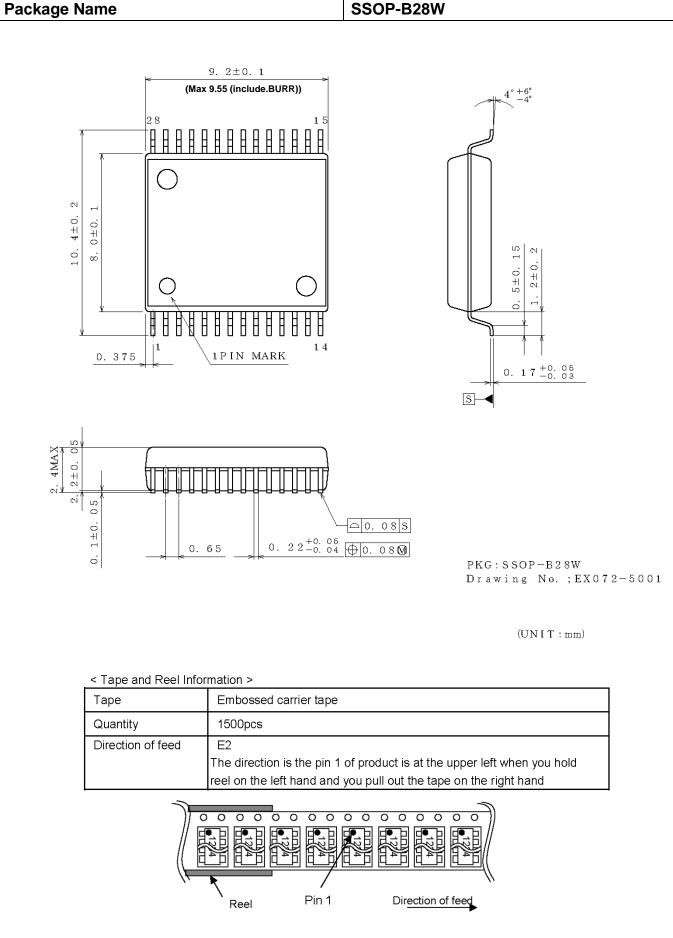


#### **Marking Diagram**



## Physical Dimension, Tape and Reel Information

## Package Name



## **Revision History**

Date	Revision	Changes
10.Apr.2015	001	New Release
25.Dec.2015	002	Page 7 Adding UL1577 Rating Table Page15 Misprint correction of Description of Pins and Cautions on Layout of Board (7)FLT Page17 Misprint correction of Description of Functions and Examples of Constant Setting (1)Miller Clamp Function

# Notice

#### **Precaution on using ROHM Products**

1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment <sup>(Note 1)</sup>, aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

JAPAN	USA	EU	CHINA
CLASSII	CLASSI	CLASS II b	CLASSⅢ
CLASSⅣ		CLASSⅢ	

2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:

[a] Installation of protection circuits or other protective devices to improve system safety

[b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure

- 3. Our Products are not designed under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

#### **Precaution for Product Label**

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

#### **Precaution for Disposition**

When disposing Products please dispose them properly using an authorized industry waste company.

#### Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

#### **Precaution Regarding Intellectual Property Rights**

- 1. All information and data including but not limited to application example contained in this document is for reference only. ROHM does not warrant that foregoing information or data will not infringe any intellectual property rights or any other rights of any third party regarding such information or data.
- 2. ROHM shall not have any obligations where the claims, actions or demands arising from the combination of the Products with other articles such as components, circuits, systems or external equipment (including software).
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#### **Other Precaution**

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- 2. The Products may not be disassembled, converted, modified, reproduced or otherwise changed without prior written consent of ROHM.
- 3. In no event shall you use in any way whatsoever the Products and the related technical information contained in the Products or this document for any military purposes, including but not limited to, the development of mass-destruction weapons.
- 4. The proper names of companies or products described in this document are trademarks or registered trademarks of ROHM, its affiliated companies or third parties.

#### **General Precaution**

- 1. Before you use our Products, you are requested to care fully read this document and fully understand its contents. ROHM shall not be in an y way responsible or liable for failure, malfunction or accident arising from the use of a ny ROHM's Products against warning, caution or note contained in this document.
- 2. All information contained in this docume nt is current as of the issuing date and subject to change without any prior notice. Before purchasing or using ROHM's Products, please confirm the latest information with a ROHM sale s representative.
- 3. The information contained in this document is provided on an "as is" basis and ROHM does not warrant that all information contained in this document is accurate an d/or error-free. ROHM shall not be in an y way responsible or liable for any damages, expenses or losses incurred by you or third parties resulting from inaccuracy or errors of or concerning such information.